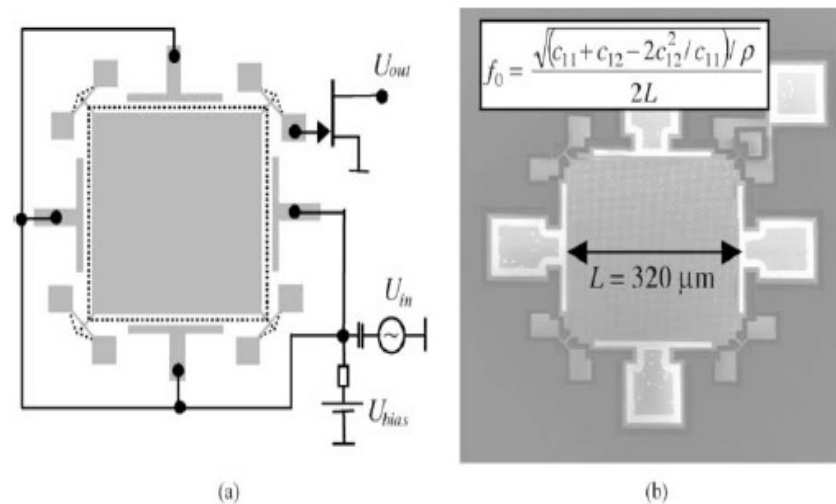


In-plane bulk-mode resonators (Lamé, breathing...)

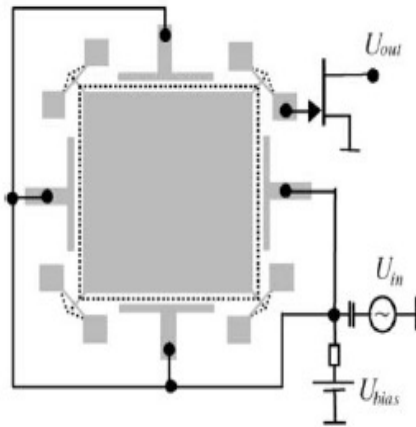


Here $h=10\ \mu\text{m}$ thick

Fig. 1. Square-extensional microresonator ($f_0 = 13.1\ \text{MHz}$ and $Q = 130\,000$). (a) Schematic of the resonator showing the vibration mode in the expanded shape and biasing and driving setup. (b) SEM image of the resonator.

V. Kaajakari et al., « Square-Extensional Mode Single-Crystal Silicon Micromechanical Resonator for Low-Phase-Noise Oscillator Applications », IEEE ELECTRON DEVICE LETTERS, VOL. 25, NO. 4, 2004

Bulk mode: large mass, high Q, can make as thick as technology allows



$320 \times 320 \times 10 \text{ } \mu\text{m}^3$

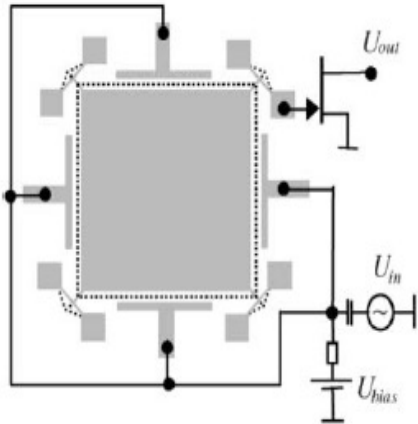
For this mode, the spring constant is:

$$k = \pi^2 Y_{2D} h$$

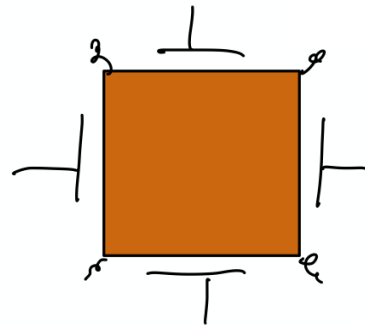
With $Y_{2D} = 181 \text{ GPa}$

1. Compute f_{res} for given dimensions
2. How does f_{res} depend on h ?

$$Y_{2D} = c_{11} + c_{12} - 2 \frac{c_{12}^2}{c_{11}} = 181 \text{ GPa}$$



$$320 \times 320 \times 10 \text{ } \mu\text{m}^3$$



$$m = \rho h L^2$$

ρ : density
 h : Si height

$$k = \frac{\pi^2}{20} \gamma h \rightarrow \text{prop to } h$$

$$\gamma_{20} = C_{11} + C_{12} - 2C_{12}^2/C_{11} = 181 \text{ GPa}$$

$$\omega_s = \sqrt{\frac{k}{m}} = \sqrt{\frac{\pi^2 \gamma_{20} h}{\rho h L^2}} = \frac{\pi}{L} \sqrt{\frac{\gamma}{\rho}}$$

no more h
dependence!

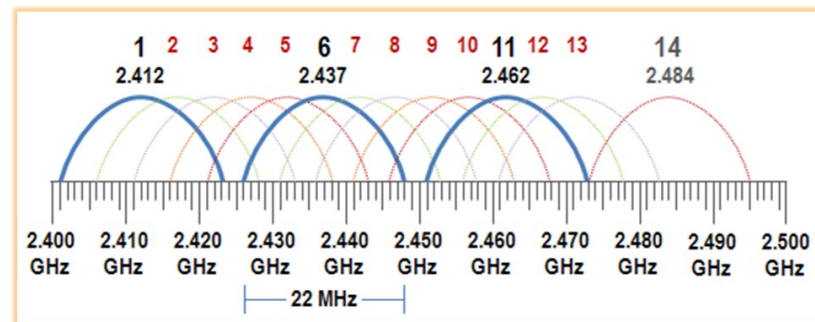
$$L = 320 \text{ } \mu\text{m} \quad \rho = 2300 \text{ kg/m}^3 \quad \gamma = 180 \text{ GPa}$$

$$\omega = \frac{\pi}{320 \cdot 10^{-6}} \sqrt{\frac{180 \cdot 10^9}{2300}} = 8.6 \cdot 10^7$$

$$f = \frac{\omega}{2\pi} = 13.8 \text{ MHz}$$

Frequency

- If we allow max 0.1% change in frequency, how much change in L can be tolerated?
- Is this feasible? (= how well can we control L?)



if want 0.1% freq shift, what change in L ?

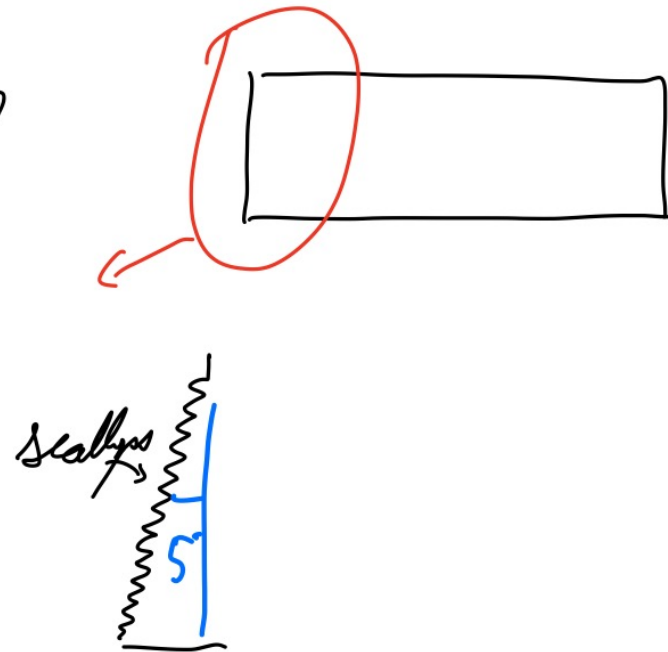
$$(f_1 - f_0) = 10^{-3} f_0 \quad f_1 = 1.001 f_0$$

$$\frac{\pi}{L_1} \sqrt{\frac{\gamma}{\rho}} = 1.001 \sqrt{\frac{\gamma}{\rho}} \frac{\pi}{L_0}$$

$$L_1 = \frac{L_0}{1.001} \rightarrow 0.1\% \text{ change in } L$$

how well do we control L ?

$320 \pm 5 \mu\text{m}$? depends on
litho and etch



Motion due to ES force

- Compute k . how does this compare to spring constants you usually see in MEMS? Stiffer? Softer?
- compute the electrostatic force from the bias voltage only
 - Gap is $0.75\text{ }\mu\text{m}$,
 - electrode length is $290\text{ }\mu\text{m}$,
 - Bias voltage = 100 V .
- compute the electrostatic force from the AC voltage
 - $Q=6200$
 - $V_{ac} = 1\text{ V}$
- Compute the static displacement due to the bias voltage . Comments?

$$h = \pi^2 / 20 \hbar$$

$$= \pi^2 180 \cdot 10^9 \cdot 10 \cdot 10^{-6}$$

$$= 2 \cdot 10^7 \text{ N/m} \text{ this is huge!}$$

$$F_{ES} = \epsilon_R \epsilon_0 \frac{A}{d^2} V_p^2$$

STATIC

$$= \epsilon_R \epsilon_0 \frac{290 \cdot 10^{-6} \cdot 10 \cdot 10^{-6} \cdot (100)^2}{[0.75 \cdot 10^{-6}]^2}$$

$$= \frac{1 \cdot 10^{-11} \cdot 300 \cdot 10^{-7}}{(0.75)^2 \cdot 10^{-12}} = \frac{3 \cdot 10^{-4}}{(0.75)^2} \text{ N}$$

$$= 0.5 \text{ mN}$$

$$\chi = \frac{F_{ES}}{h} = \frac{5 \cdot 10^{-4}}{2 \cdot 10^7} = 2.5 \cdot 10^{-11} \text{ m}$$

$$= 0.025 \text{ nm}$$

only from V_p

$$F_{ES} \propto h$$
$$k \propto h$$

$$\chi = \frac{F_{ES}}{k} \propto \frac{h}{h} \propto h^0$$

no dependence of χ on h
to first order

$$F_{ES} = \left[\frac{1}{2} V_p^2 + V_p V_{AC} \right] \frac{\epsilon_0 \epsilon_r A}{d^2}$$

$$= 30 \text{ mN at } A_c$$

$$|x_{AC}| = Q \frac{V_p V_D}{R} \frac{\epsilon_0 A}{d^2}$$

$$d = 0.75 \mu\text{m} \quad A = 320 \mu\text{m} \times 10 \mu\text{m} \quad V_{AC} = 1 \text{ V}$$

$$|x_{AC}| = \frac{6200 \cdot 100 \cdot 1 \cdot 10^{-18} \cdot 3.2 \cdot 10^{-4} \times 10^{-5}}{2 \cdot 10^7 \cdot (7.5 \cdot 10^{-7})^2} = 1.5 \text{ nm}$$

Thermal vs. mechanical energy

- At resonance, we have $x_{\text{vib}} = 1.5 \text{ nm}$
- Compare thermal energy and mechanical energy. Your comments?
- E_{mech} : how does it scale with h ? With V ?
- How low would the bias voltage have to be to have: $E_{\text{mech}} = 100 \times E_{\text{thermal}}$?

compare thermal E_{th} to mechanical energy E_m

$$x_{vib} = 1.5 \text{ nm (including Q)}$$

$$P_{dune} = 0.12 \text{ mW}$$

then goes hysteretic

$$k = \pi^2 \gamma_{20} h$$

$$E_m = \frac{1}{2} k x^2 = \frac{1}{2} \pi^2 \gamma h x^2 = \frac{1}{2} \pi^2 180 \cdot 10^9 \cdot 10 \cdot 10^{-6} \cdot (1.5 \times 10^{-9})^2 = 2 \cdot 10^{-11} \text{ J}$$

$$E_{th} = \frac{1}{2} k_B T = \frac{1}{2} \cdot 10^{-23} \cdot 300 = 10^{-21} \text{ J}$$

$$E_m / E_{th} = 2 \cdot 10^{-11} / 10^{-21} = 2 \cdot 10^{10}$$

$$E_{mech} \gg E_{th}$$

Now we set $E_m/E_{th} = 100$

$$E_m \propto x^2 \text{ and } x \propto V^2 \rightarrow E_m \propto V^4,$$

so if reduce $\frac{E_m}{E_{th}}$ from 10^{10} to 10^2 $V = 100 \cdot (10^{-12})^{1/4} = 0.1V$

$$V = V_{old} \cdot \left[10^2 / 10^{14} \right]^{1/4} = 100 \cdot (10^{-8})^{1/4} = 1V$$

$\left. \begin{array}{l} F_{ES} \propto h \\ h \propto h \end{array} \right\} \rightarrow x_{vib} \text{ does not depend on } h. \text{ so } \underline{E_{mech} \propto h}$

need to choose a thick enough plate to ensure can excite the desired mode